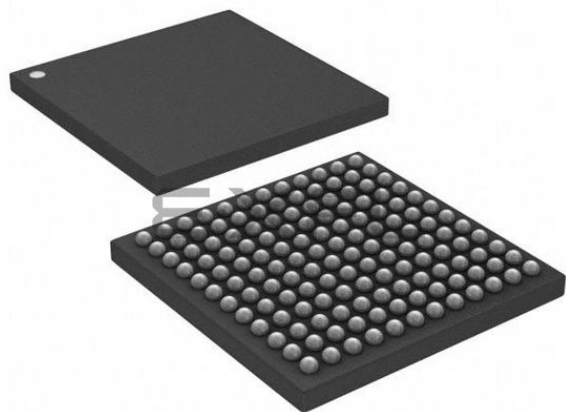




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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	112
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-UFBGA
Supplier Device Package	144-UFBGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f723zci6

Table 41.	HSE 4-26 MHz oscillator characteristics	133
Table 42.	LSE oscillator characteristics ($f_{LSE} = 32.768 \text{ kHz}$)	134
Table 43.	HSI oscillator characteristics	136
Table 44.	LSI oscillator characteristics	137
Table 45.	Main PLL characteristics	137
Table 46.	PLLI2S characteristics	138
Table 47.	PLLI2S characteristics	139
Table 48.	SSCG parameters constraint	140
Table 49.	USB OTG HS PLL1 characteristics	142
Table 50.	USB OTG HS PLL2 characteristics	142
Table 51.	USB OTG HS PHY regulator characteristics	142
Table 52.	USB HS PHY external resistor characteristics (on STM32F723xx devices)	143
Table 53.	Flash memory characteristics	143
Table 54.	Flash memory programming	143
Table 55.	Flash memory programming with VPP	144
Table 56.	Flash memory endurance and data retention	144
Table 57.	EMS characteristics	145
Table 58.	EMI characteristics	146
Table 59.	ESD absolute maximum ratings	147
Table 60.	Electrical sensitivities	147
Table 61.	I/O current injection susceptibility	148
Table 62.	I/O static characteristics	148
Table 63.	Output voltage characteristics	151
Table 64.	I/O AC characteristics	152
Table 65.	NRST pin characteristics	154
Table 66.	TIMx characteristics	155
Table 67.	RTC characteristics	155
Table 68.	ADC characteristics	155
Table 69.	ADC static accuracy at $f_{ADC} = 18 \text{ MHz}$	157
Table 70.	ADC static accuracy at $f_{ADC} = 30 \text{ MHz}$	157
Table 71.	ADC static accuracy at $f_{ADC} = 36 \text{ MHz}$	158
Table 72.	ADC dynamic accuracy at $f_{ADC} = 18 \text{ MHz}$ - limited test conditions	158
Table 73.	ADC dynamic accuracy at $f_{ADC} = 36 \text{ MHz}$ - limited test conditions	158
Table 74.	Temperature sensor characteristics	161
Table 75.	Temperature sensor calibration values	161
Table 76.	V_{BAT} monitoring characteristics	161
Table 77.	internal reference voltage	161
Table 78.	Internal reference voltage calibration values	162
Table 79.	DAC characteristics	162
Table 80.	Minimum I2CCLK frequency in all I2C modes	164
Table 81.	I2C analog filter characteristics	165
Table 82.	SPI dynamic characteristics	166
Table 83.	I ² S dynamic characteristics	169
Table 84.	SAI characteristics	171
Table 85.	USB OTG full speed startup time	173
Table 86.	USB OTG full speed DC electrical characteristics	173
Table 87.	USB OTG full speed electrical characteristics	174
Table 88.	USB HS DC electrical characteristics	174
Table 89.	USB HS clock timing parameters	175
Table 90.	Dynamic characteristics: USB ULPI	176
Table 91.	USB OTG high speed DC electrical characteristics	176
Table 92.	USB OTG high speed electrical characteristics	176

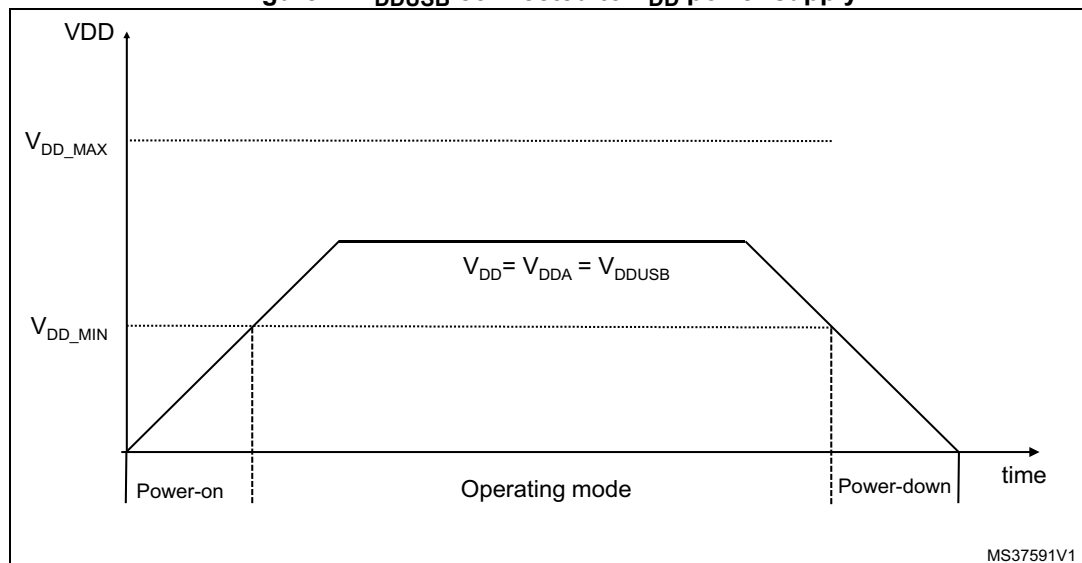
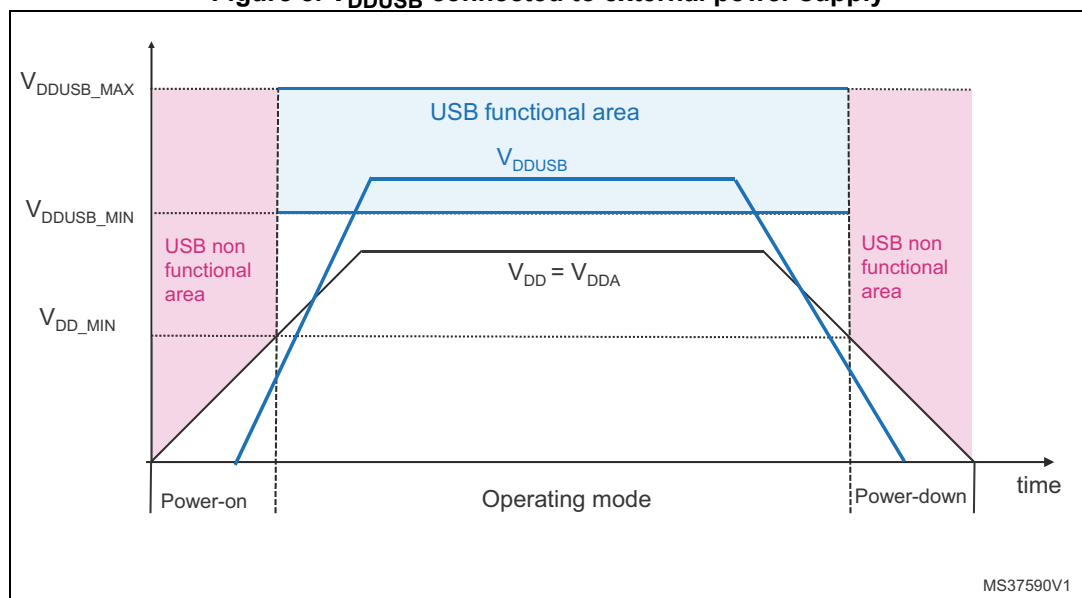
Table 93.	USB FS PHY BCD electrical characteristics	177
Table 94.	Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings	179
Table 95.	Asynchronous non-multiplexed SRAM/PSRAM/NOR read - NWAIT timings	179
Table 96.	Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings	180
Table 97.	Asynchronous non-multiplexed SRAM/PSRAM/NOR write - NWAIT timings	181
Table 98.	Asynchronous multiplexed PSRAM/NOR read timings	182
Table 99.	Asynchronous multiplexed PSRAM/NOR read-NWAIT timings	182
Table 100.	Asynchronous multiplexed PSRAM/NOR write timings	183
Table 101.	Asynchronous multiplexed PSRAM/NOR write-NWAIT timings	184
Table 102.	Synchronous multiplexed NOR/PSRAM read timings	186
Table 103.	Synchronous multiplexed PSRAM write timings	188
Table 104.	Synchronous non-multiplexed NOR/PSRAM read timings	189
Table 105.	Synchronous non-multiplexed PSRAM write timings	191
Table 106.	Switching characteristics for NAND Flash read cycles	193
Table 107.	Switching characteristics for NAND Flash write cycles	193
Table 108.	SDRAM read timings	195
Table 109.	LPDDR SDRAM read timings	195
Table 110.	SDRAM write timings	196
Table 111.	LPDDR SDRAM write timings	197
Table 112.	Quad-SPI characteristics in SDR mode	197
Table 113.	Quad-SPI characteristics in DDR mode	198
Table 114.	Dynamic characteristics: SD / MMC characteristics, VDD=2.7V to 3.6V	200
Table 115.	Dynamic characteristics: eMMC characteristics, VDD=1.71V to 1.9V	201
Table 116.	LQFP64 – 10 x 10 mm, low-profile quad flat package mechanical data	202
Table 117.	LQFP100, 14 x 14 mm 100-pin low-profile quad flat package mechanical data	205
Table 118.	LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package mechanical data	208
Table 119.	LQFP176, 24 x 24 mm, 176-pin low-profile quad flat package mechanical data	211
Table 120.	UFBGA144 - 144-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data	215
Table 121.	UFBGA144 recommended PCB design rules (0.50 mm pitch BGA)	216
Table 122.	UFBGA176+25, 10 x 10 x 0.65 mm ultra thin fine-pitch ball grid array package mechanical data	218
Table 123.	UFBGA176+25 recommended PCB design rules (0.65 mm pitch BGA)	219
Table 124.	WLCSP100 – 100L, 4.166 x 4.628 mm 0.4 mm pitch wafer level chip scale package mechanical data	222
Table 125.	WLCSP100 recommended PCB design rules (0.4 mm pitch)	223
Table 126.	Package thermal characteristics	225
Table 127.	Ordering information scheme	226
Table 128.	Limitations depending on the operating power supply range	227
Table 129.	Document revision history	228

Table 2. STM32F722xx and STM32F723xx features and peripheral counts (continued)

Peripherals	STM32F72xRx	STM32F72xVx	STM32F72xZx	STM32F72xLx
Operating voltage	1.7 to 3.6 V ⁽⁸⁾			
Operating temperatures	Ambient temperatures: –40 to +85 °C / –40 to +105 °C			
	Junction temperature: –40 to + 125 °C			
Package	LQFP64 ⁽⁹⁾	LQFP100 ⁽⁹⁾ WLCSP100 ⁽¹⁰⁾	LQFP144 UFBGA144 ⁽¹⁰⁾	UFBGA176 LQFP176

1. For the LQFP100 package, only FMC Bank1 is available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select.
2. On the STM32F723xx device packages, except the 176-pin ones, the TIM12 is not available, so there are 9 general-purpose timers.
3. The SPI1, SPI2 and SPI3 interfaces give the flexibility to work in an exclusive way in either the SPI mode or the I²S audio mode.
4. USB OTG HS with the ULPI on the STM32F722xx devices and with integrated HS PHY on the STM32F723xx devices.
5. The SDMMC2 supports a dedicated power rail for clock, command and data 0..4 lines, feature available starting from 144 pin package.
6. The SDMMC2 is not available on the STM32F723Vx devices.
7. 216 MHz maximum frequency for - 40°C to + 85°C ambient temperature range (200 MHz maximum frequency for - 40°C to + 105°C ambient temperature range).
8. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the internal reset is OFF (refer to [Section 2.15.2: Internal reset OFF](#)).
9. Available only on the STM32F722xx devices.
10. Available only on the STM32F723xx devices.

- The V_{DDUSB} rising and falling time rate specifications must be respected
- In the operating mode phase, V_{DDUSB} could be lower or higher than V_{DD} :
 - If the USB (USB OTG_HS/OTG_FS) is used, the associated GPIOs powered by V_{DDUSB} are operating between V_{DDUSB_MIN} and V_{DDUSB_MAX} .
 - The V_{DDUSB} supplies both USB transceiver (USB OTG_HS and USB OTG_FS). If only one USB transceiver is used in the application, the GPIOs associated to the other USB transceiver are still supplied by V_{DDUSB} .
 - If the USB (USB OTG_HS/OTG_FS) is not used, the associated GPIOs powered by V_{DDUSB} are operating between V_{DD_MIN} and V_{DD_MAX} .

Figure 7. V_{DDUSB} connected to V_{DD} power supplyFigure 8. V_{DDUSB} connected to external power supply

2.29 Universal serial bus on-the-go full-speed (OTG_FS)

The device embeds an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 2.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator.

The major features are:

- Combined Rx and Tx FIFO size of 1.28 Kbytes with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 1 bidirectional control endpoint + 5 IN endpoints + 5 OUT endpoints
- 12 host channels with periodic OUT support
- Software configurable to OTG1.3 and OTG2.0 modes of operation
- USB 2.0 LPM (Link Power Management) support
- Internal FS OTG PHY support
- HNP/SNP/IP inside (no need for any external resistor)
- BCD support

For the OTG/Host modes, a power switch is needed in case bus-powered devices are connected

2.30 Universal serial bus on-the-go high-speed (OTG_HS)

The device embeds an USB OTG high-speed (up to 480 Mbit/s) device/host/OTG peripheral. The USB OTG HS supports both full-speed and high-speed operations. It integrates the transceivers for full-speed operation (12 Mbit/s).

The STM32F722xx devices feature a UTMI low-pin interface (ULPI) for high-speed operation (480 Mbit/s). When using the USB OTG HS in HS mode, an external PHY device connected to the ULPI is required.

The STM32F723xx devices feature an integrated PHY HS.

The USB OTG HS peripheral is compliant with the USB 2.0 specification and with the OTG 2.0 specification. It has a software-configurable endpoint setting and supports suspend/resume. The USB OTG controller requires a dedicated 48 MHz clock that is generated by a PLL connected to the HSE oscillator.

The major features are:

- Combined Rx and Tx FIFO size of 4 Kbytes with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 8 bidirectional endpoints
- 16 host channels with periodic OUT support
- Software configurable to OTG1.3 and OTG2.0 modes of operation
- USB 2.0 LPM (Link Power Management) support
- **For the STM32F722xx devices:** External HS or HS OTG operation supporting ULPI in SDR mode. The OTG PHY is connected to the microcontroller ULPI port through 12 signals. It can be clocked using the 60 MHz output.
- **For the STM32F723xx devices:** Internal HS OTG PHY support.

- Internal USB DMA
- HNP/SNP/IP inside (no need for any external resistor)
- For OTG/Host modes, a power switch is needed in case bus-powered devices are connected

Universal Serial Bus controller on-the-go High-Speed PHY controller (USBPHYC) only on STM32F723xx devices.

The USB HS PHY controller:

- Sets the PHYPLL1/2 values for the PHY HS
- Sets the other controls on the PHY HS
- Controls and monitors the USB PHY's LDO

2.31 Random number generator (RNG)

All the devices embed an RNG that delivers 32-bit random numbers generated by an integrated analog circuit.

2.32 General-purpose input/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain, with or without pull-up or pull-down), as input (floating, with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current-capable and have speed selection to better manage internal noise, power consumption and electromagnetic emission.

The I/O configuration can be locked if needed by following a specific sequence in order to avoid spurious writing to the I/Os registers.

A Fast I/O handling allows a maximum I/O toggling up to 108 MHz.

2.33 Analog-to-digital converters (ADCs)

Three 12-bit analog-to-digital converters are embedded and each ADC shares up to 16 external channels, performing conversions in the single-shot or scan mode. In the scan mode, an automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold

The ADC can be served by the DMA controller. An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

To synchronize A/D conversion and timers, the ADCs could be triggered by any of TIM1, TIM2, TIM3, TIM4, TIM5, or TIM8 timer.

Table 10. STM32F722xx and STM32F723xx pin and ball definition (continued)

Pin Number										Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F722xx					STM32F723xx										
LQFP64	LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP100	UFBGA176	UFBGA144	LQFP144	LQFP176						
-	-	-	C9	136	-	C9	-	-	136	VDD	S	-	-	-	-
49	76	109	A14	137	C4	A14	A11	109	137	PA14(JTCK-SWCLK)	I/O	FT	-	JTCK-SWCLK, EVENTOUT	-
50	77	110	A13	138	B4	A13	A10	110	138	PA15(JTDI)	I/O	FT	-	JTDI, TIM2_CH1/TIM2_ETR, SPI1_NSS/I2S1_WS, SPI3_NSS/I2S3_WS, UART4_RTS, EVENTOUT	-
51	78	111	B14	139	A3	B14	B11	111	139	PC10	I/O	FT	-	SPI3_SCK/I2S3_CK, USART3_TX, UART4_TX, QUADSPI_BK1_IO1, SDMMC1_D2, EVENTOUT	-
52	79	112	B13	140	C5	B13	B10	112	140	PC11	I/O	FT	-	SPI3_MISO, USART3_RX, UART4_RX, QUADSPI_BK2_NCS, SDMMC1_D3, EVENTOUT	-
53	80	113	A12	141	D5	A12	C10	113	141	PC12	I/O	FT	-	TRACED3, SPI3_MOSI/I2S3_SD, USART3_CK, UART5_TX, SDMMC1_CK, EVENTOUT	-
-	81	114	B12	142	B5	B12	E10	114	142	PD0	I/O	FT	-	CAN1_RX, FMC_D2, EVENTOUT	-
-	82	115	C12	143	A4	C12	D10	115	143	PD1	I/O	FT	-	CAN1_TX, FMC_D3, EVENTOUT	-

Table 12. STM32F722xx and STM32F723xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1	I2C1/2/3/USART1	SPI1/I2S1/SPI2/I2S2/SPI3/I2S3/SPI4/5	SPI2/I2S2/SPI3/I2S3/SPI1/UART4	SPI2/I2S2/SPI3/I2S3/USART1/2/3/UART5	SAI2/USART6/UART4/5/7/8/OTG1_FS	CAN1/TIM12/13/14/QUADSPI/ADSPI/FMC/OTG2_HS	SAI2/QUADSPI/SDMMC2/OTG2_HS/OTG1_FS	SDMMC2	UART7/FMC/SDMMC1/OTG2_FS	SYS
Port H	PH8	-	-	-	-	I2C3_SDA	-	-	-	-	-	-	-	FMC_D16	EVEN TOUT
	PH9	-	-	-	-	I2C3_SMB_A	-	-	-	-	TIM12_CH2	-	-	FMC_D17	EVEN TOUT
	PH10	-	-	TIM5_CH1	-	-	-	-	-	-	-	-	-	FMC_D18	EVEN TOUT
	PH11	-	-	TIM5_CH2	-	-	-	-	-	-	-	-	-	FMC_D19	EVEN TOUT
	PH12	-	-	TIM5_CH3	-	-	-	-	-	-	-	-	-	FMC_D20	EVEN TOUT
	PH13	-	-	-	TIM8_CH1_N	-	-	-	-	UART4_TX	CAN1_TX	-	-	FMC_D21	EVEN TOUT
	PH14	-	-	-	TIM8_CH2_N	-	-	-	-	UART4_RX	CAN1_RX	-	-	FMC_D22	EVEN TOUT
	PH15	-	-	-	TIM8_CH3_N	-	-	-	-	-	-	-	-	FMC_D23	EVEN TOUT
Port I	PI0	-	-	TIM5_CH4	-	-	SPI2_NSS/I2S2_WS	-	-	-	-	-	-	FMC_D24	EVEN TOUT
	PI1	-	-	-	TIM8_BKIN2	-	SPI2_SCK/I2S2_CK	-	-	-	-	-	-	FMC_D25	EVEN TOUT
	PI2	-	-	-	TIM8_CH4	-	SPI2_MISO	-	-	-	-	-	-	FMC_D26	EVEN TOUT
	PI3	-	-	-	TIM8_ETR	-	SPI2_MOSI/I2S2_SD	-	-	-	-	-	-	FMC_D27	EVEN TOUT
	PI4	-	-	-	TIM8_BKIN	-	-	-	-	-	-	SAI2_MCK_A	-	FMC_NBL2	EVEN TOUT
	PI5	-	-	-	TIM8_CH1	-	-	-	-	-	-	SAI2_SCK_A	-	FMC_NBL3	EVEN TOUT
	PI6	-	-	-	TIM8_CH2	-	-	-	-	-	-	SAI2_SD_A	-	FMC_D28	EVEN TOUT

Table 13. STM32F722xx and STM32F723xx register boundary addresses⁽¹⁾

Bus	Boundary address	Peripheral
	0xE00F FFFF - 0xFFFF FFFF	Reserved
Cortex-M7	0xE000 0000 - 0xE00F FFFF	Cortex-M7 internal peripherals
AHB3	0xD000 0000 - 0xDFFF FFFF	FMC bank 6
	0xC000 0000 - 0xCFFF FFFF	FMC bank 5
	0xA000 2000 - 0xBFFF FFFF	Reserved
	0xA000 1000 - 0xA000 1FFF	Quad-SPI control register
	0xA000 0000 - 0xA000 0FFF	FMC control register
	0x9000 0000 - 0x9FFF FFFF	Quad-SPI
	0x8000 0000 - 0x8FFF FFFF	FMC bank 3
	0x7000 0000 - 0x7FFF FFFF	FMC bank 2
	0x6000 0000 - 0x6FFF FFFF	FMC bank 1
	0x5006 0C00 - 0x5FFF FFFF	Reserved
AHB2	0x5006 0800 - 0x5006 0BFF	RNG
	0x5004 0000 - 0x5006 07FF	Reserved
	0x5000 0000 - 0x5003 FFFF	USB OTG FS

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load).
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted both to f_{HCLK} frequency and V_{DD} range (see [Table 18: Limitations depending on the operating power supply range](#)).
- When the regulator is ON, the voltage scaling and over-drive mode are adjusted to f_{HCLK} frequency as follows:
 - Scale 3 for $f_{HCLK} \leq 144$ MHz
 - Scale 2 for $144 \text{ MHz} < f_{HCLK} \leq 168$ MHz
 - Scale 1 for $168 \text{ MHz} < f_{HCLK} \leq 216$ MHz. The over-drive is only ON at 216 MHz.
- When the regulator is OFF, the V12 is provided externally as described in [Table 17: General operating conditions](#):
- The system clock is HCLK, $f_{PCLK1} = f_{HCLK}/4$, and $f_{PCLK2} = f_{HCLK}/2$.
- External clock frequency is 25 MHz and PLL is ON when f_{HCLK} is higher than 25 MHz.
- The typical current consumption values are obtained for $1.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$ voltage range and for $T_A = 25^\circ\text{C}$ unless otherwise specified.
- The maximum values are obtained for $1.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$ voltage range and a maximum ambient temperature (T_A) unless otherwise specified.
- For the voltage range $1.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$, the maximum frequency is 180 MHz.

Table 25. Typical and maximum current consumption in Run mode, code with data processing running from ITCM RAM, regulator ON

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
					$T_A = 25^\circ\text{C}$	$T_A = 85^\circ\text{C}$	$T_A = 105^\circ\text{C}$	
I_{DD}	Supply current in RUN mode	All peripherals enabled ⁽²⁾⁽³⁾	216	156	170 ⁽⁴⁾	180 ⁽⁴⁾	200	mA
			200	144	154	164.6	183	
			180	127	134 ⁽⁴⁾	143 ⁽⁴⁾	158 ⁽⁴⁾	
			168	113	119	127.4	141	
			144	86	96	112.6	126	
			60	41	44	52.8	65	
			25	22	24	33.5	45	
		All peripherals disabled ⁽³⁾	216	99	110 ⁽⁴⁾	119.6 ⁽⁴⁾	138.5	
			200	92	102	113.1	132	
			180	81	90 ⁽⁴⁾	96.7 ⁽⁴⁾	125 ⁽⁴⁾	
			168	72	78	86.5	100.1	
			144	55	61	77.1	90.8	
			60	24	25	38.5	50.3	
			25	12	13	26.3	38.1	

1. Guaranteed by characterization results.

- When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
- When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.
- Guaranteed by test in production.

Table 26. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART ON except prefetch / L1-cache ON) or SRAM on AXI (L1-cache ON), regulator ON

Symbol	Parameter	Conditions	f _{HCLK} (MHz)	Typ	Max ⁽¹⁾			Unit
					T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in RUN mode	All peripherals enabled ⁽²⁾⁽³⁾	216	155.3	164	175.8	185	mA
			200	144.7	153.6	165.2	176	
			180	127.3	135	143.5	154	
			168	113.1	119.1	127.8	138	
			144	86.9	91.6	99.5	110	
			60	41.2	43.6	53.1	64	
			25	21.7	24	33.6	43.8	
		All peripherals disabled ⁽³⁾	216	90	106	120.4	130	
			200	84	99	113.8	124	
			180	74	86.6	97.3	107	
			168	66	76	87	97	
			144	51	59	68.2	78	
			60	23	27	38.8	49	
			25	11	13.6	26.4	36.8	

- Guaranteed by characterization results.
- When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
- When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.73 mA per ADC for the analog part.

Figure 31. Typical V_{BAT} current consumption (RTC ON/BKP SRAM OFF and LSE in low drive mode)

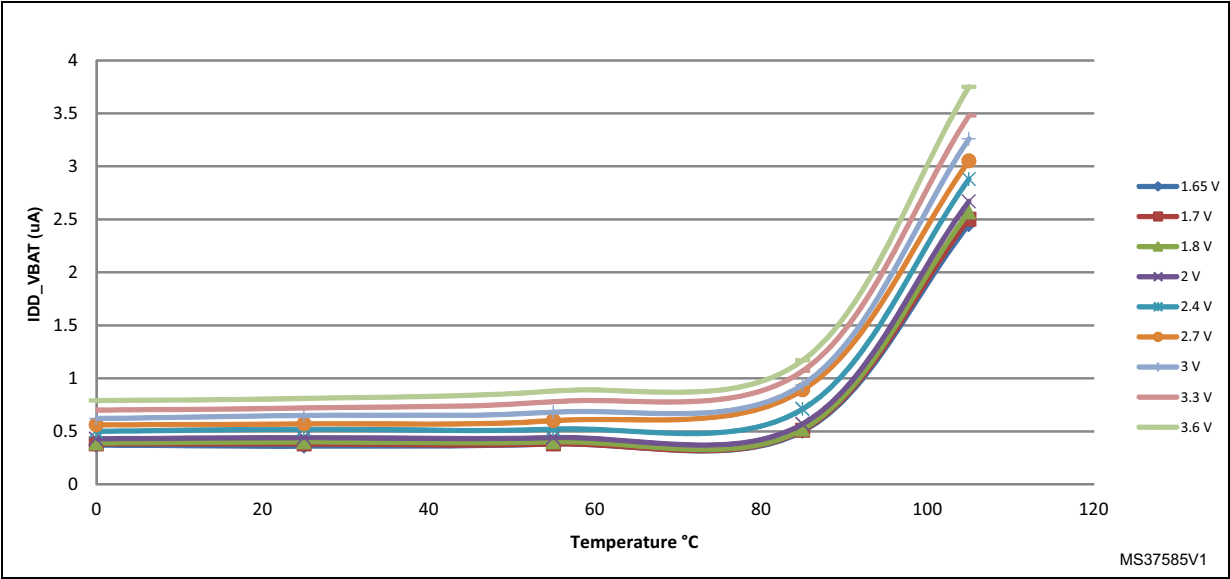


Figure 32. Typical V_{BAT} current consumption (RTC ON/BKP SRAM OFF and LSE in medium low drive mode)

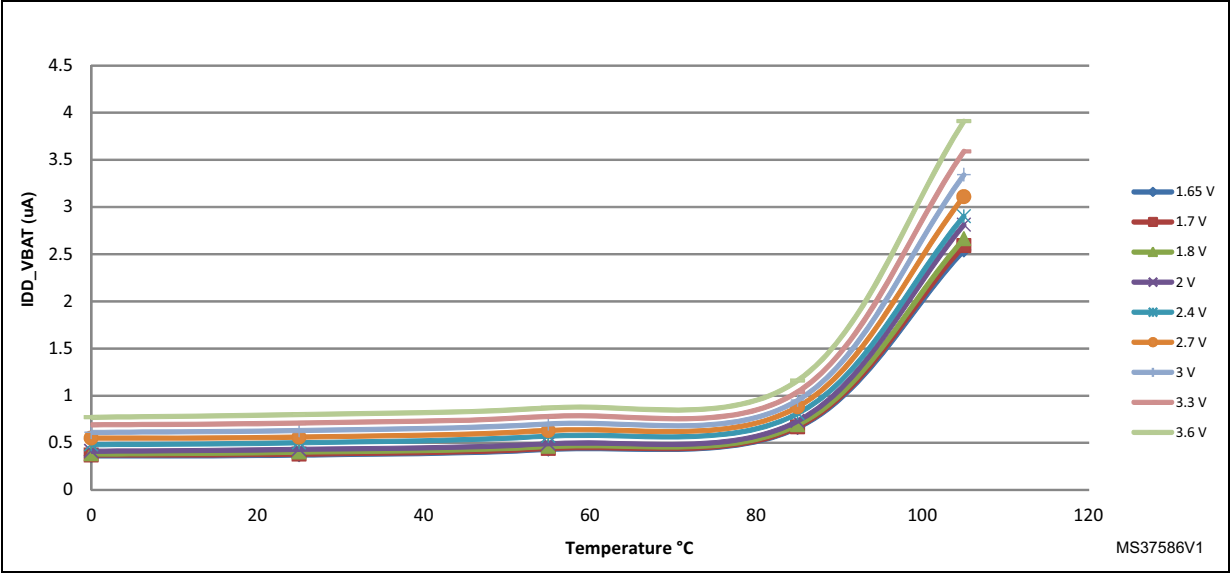
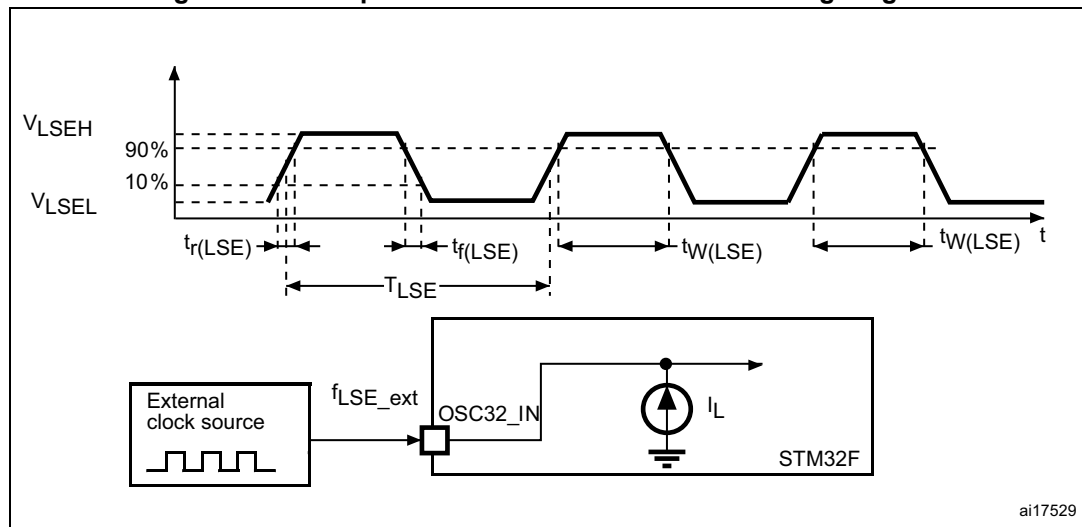


Figure 37. Low-speed external clock source AC timing diagram



ai17529

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 26 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 41](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 41. HSE 4-26 MHz oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	4	-	26	MHz
R_F	Feedback resistor	-	-	200	-	k Ω
I_{DD}	HSE current consumption	$V_{DD}=3.3\text{ V}$, ESR= 30 Ω , $C_L=5\text{ pF}@25\text{ MHz}$	-	450	-	μA
		$V_{DD}=3.3\text{ V}$, ESR= 30 Ω , $C_L=10\text{ pF}@25\text{ MHz}$	-	530	-	
$ACC_{HSE}^{(2)}$	HSE accuracy	-	- 500	-	500	ppm
$G_{m_crit_max}$	Maximum critical crystal g_m	Startup	-	-	1	mA/V
$t_{SU(HSE)}^{(3)}$	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design.

2. This parameter depends on the crystal used in the application. The minimum and maximum values must be respected to comply with USB standard specifications.

3. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is based on characterization results. It is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

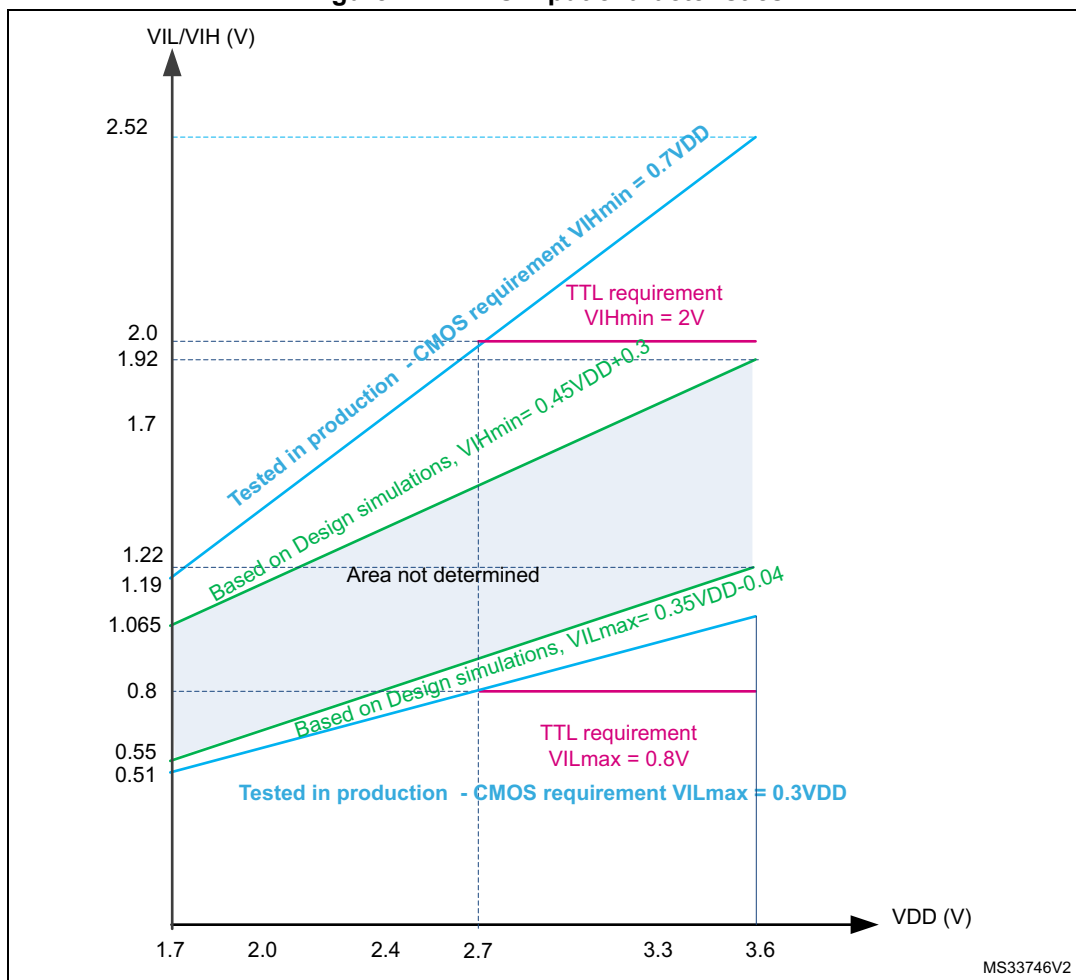
Table 62. I/O static characteristics (continued)

Symbol	Parameter		Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor ⁽⁶⁾	All pins except for PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	$V_{IN} = V_{SS}$	30	40	50	k Ω
		PA10/PB12 (OTG_FS_ID, OTG_HS_ID)		7	10	14	
R_{PD}	Weak pull-down equivalent resistor ⁽⁷⁾	All pins except for PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	$V_{IN} = V_{DD}$	30	40	50	
		PA10/PB12 (OTG_FS_ID, OTG_HS_ID)		7	10	14	
C_{IO} ⁽⁸⁾	I/O pin capacitance		-	-	5	-	pF

1. Guaranteed by design.
2. Tested in production.
3. With a minimum of 200 mV.
4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to [Table 61: I/O current injection susceptibility](#)
5. To sustain a voltage higher than VDD +0.3 V, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to [Table 61: I/O current injection susceptibility](#)
6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).
7. Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
8. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT I/Os is shown in [Figure 44](#).

Figure 44. FT I/O input characteristics



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14, PC15 and PI8 which can sink or source up to ± 3 mA. When using the PC13 to PC15 and PI8 GPIOs in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

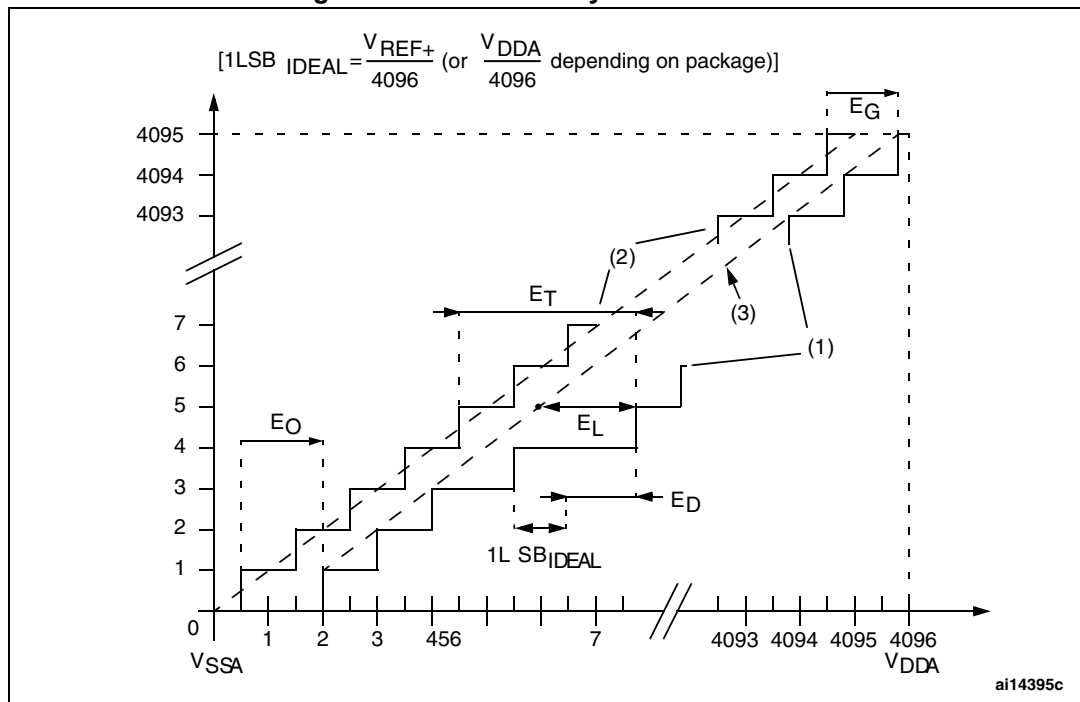
In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 5.2](#). In particular:

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating ΣI_{VDD} (see [Table 15](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see [Table 15](#)).

Output voltage levels

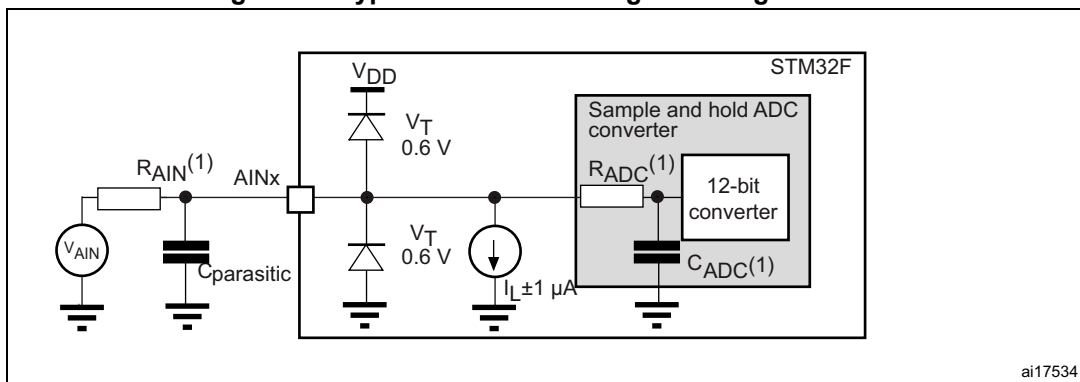
Unless otherwise specified, the parameters given in [Table 63](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 17](#). All I/Os are CMOS and TTL compliant.

Figure 47. ADC accuracy characteristics



1. See also [Table 70](#).
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
 E_O = Offset Error: deviation between the first actual transition and the first ideal one.
 E_G = Gain Error: deviation between the last ideal transition and the last actual one.
 E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
 E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 48. Typical connection diagram using the ADC



1. Refer to [Table 68](#) for the values of R_{AIN} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

5.3.25 Temperature sensor characteristics

Table 74. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$T_L^{(1)}$	V_{SENSE} linearity with temperature	-	± 1	± 2	°C
Avg_Slope ⁽¹⁾	Average slope	-	2.5	-	mV/°C
$V_{25}^{(1)}$	Voltage at 25 °C	-	0.76	-	V
$t_{START}^{(2)}$	Startup time	-	6	10	μs
$T_{S_temp}^{(2)}$	ADC sampling time when reading the temperature (1 °C accuracy)	10	-	-	μs

1. Guaranteed by characterization results.

2. Guaranteed by design.

Table 75. Temperature sensor calibration values

Symbol	Parameter	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, $V_{DDA} = 3.3$ V	0x1FF0 7A2C - 0x1FF0 7A2D
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C, $V_{DDA} = 3.3$ V	0x1FF0 7A2E - 0x1FF0 7A2F

5.3.26 V_{BAT} monitoring characteristics

Table 76. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	50	-	KΩ
Q	Ratio on V_{BAT} measurement	-	4	-	-
$E_r^{(1)}$	Error on Q	-1	-	+1	%
$T_{S_vbat}^{(2)(2)}$	ADC sampling time when reading the V_{BAT} 1 mV accuracy	5	-	-	μs

1. Guaranteed by design.

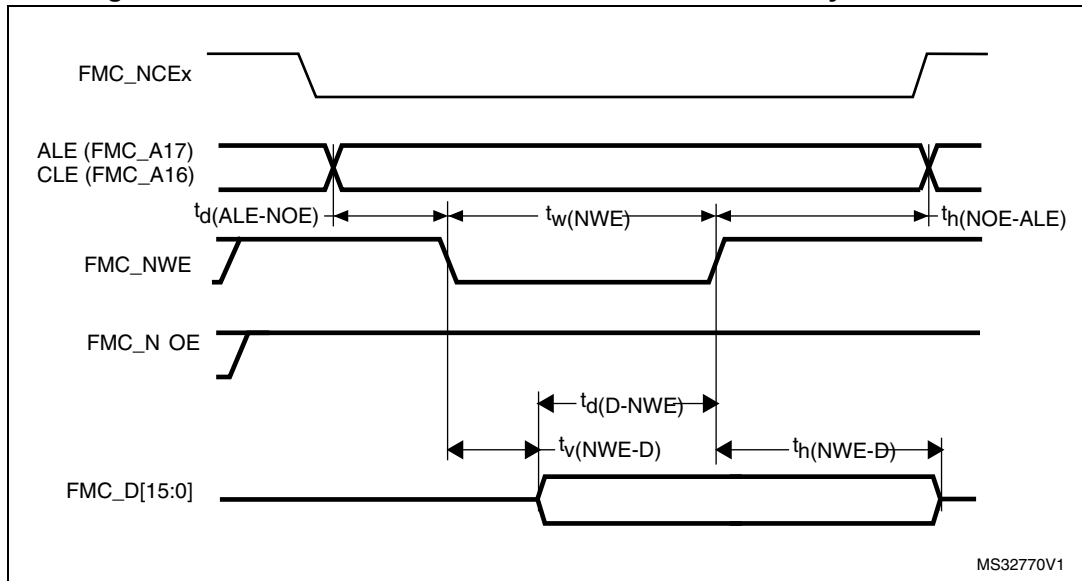
2. Shortest sampling time can be determined in the application by multiple iterations.

5.3.27 Reference voltage

The parameters given in [Table 77](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 17](#).

Table 77. internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	$-40\text{ °C} < T_A < +105\text{ °C}$	1.18	1.21	1.24	V
$T_{S_vrefint}^{(1)}$	ADC sampling time when reading the internal reference voltage	-	10	-	-	μs
$V_{RERINT_s}^{(2)}$	Internal reference voltage spread over the temperature range	$V_{DD} = 3V \pm 10mV$	-	3	5	mV

Figure 72. NAND controller waveforms for common memory write access**Table 106. Switching characteristics for NAND Flash read cycles⁽¹⁾**

Symbol	Parameter	Min	Max	Unit
$t_{w(NOE)}$	FMC_NOE low width	4Thclk - 0.5	4Thclk + 0.5	ns
$t_{su(D-NOE)}$	FMC_D[15-0] valid data before FMC_NOE high	11	-	
$t_{h(NOE-D)}$	FMC_D[15-0] valid data after FMC_NOE high	0	-	
$t_d(ALE-NOE)$	FMC_ALE valid before FMC_NOE low	-	3Thclk + 1.5	
$t_{h(NOE-ALE)}$	FMC_NWE high to FMC_ALE invalid	4Thclk - 2	-	

1. Guaranteed by characterization results.

Table 107. Switching characteristics for NAND Flash write cycles⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NWE)}$	FMC_NWE low width	4Thclk - 0.5	4Thclk + 0.5	ns
$t_{v(NWE-D)}$	FMC_NWE low to FMC_D[15-0] valid	0	-	
$t_{h(NWE-D)}$	FMC_NWE high to FMC_D[15-0] invalid	2Thclk - 1	-	
$t_d(D-NWE)$	FMC_D[15-0] valid before FMC_NWE high	5Thclk - 1	-	
$t_d(ALE-NWE)$	FMC_ALE valid before FMC_NWE low	-	3Thclk + 1.5	
$t_{h(NWE-ALE)}$	FMC_NWE high to FMC_ALE invalid	2Thclk - 2	-	

1. Guaranteed by characterization results.

Figure 75. Quad-SPI timing diagram - SDR mode

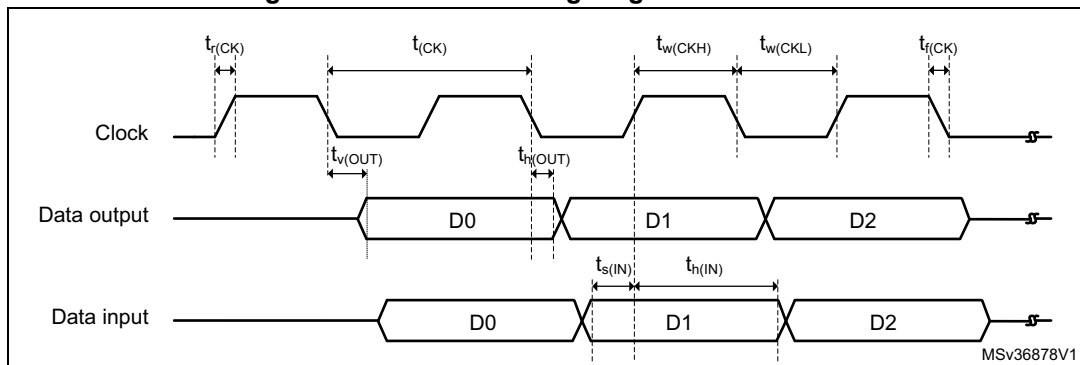
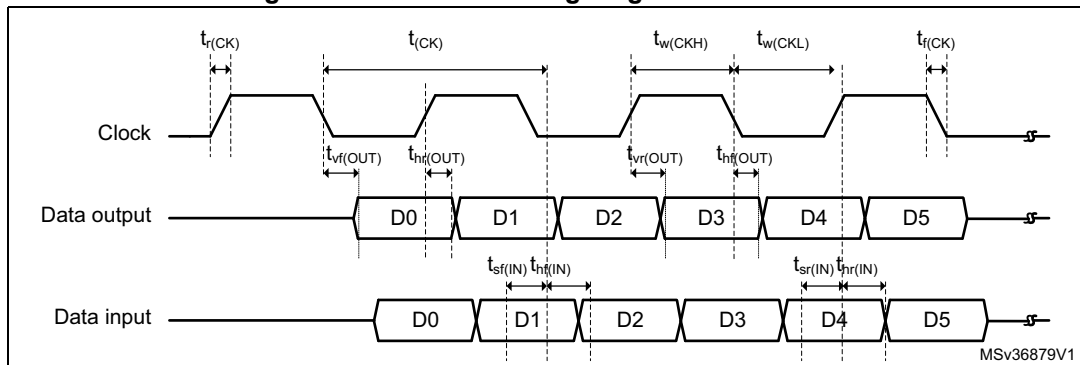


Figure 76. Quad-SPI timing diagram - DDR mode



5.3.32 SD/SDIO MMC card host interface (SDMMC) characteristics

Unless otherwise specified, the parameters given in [Table 114](#) for the SDIO/MMC interface are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DD} supply voltage conditions summarized in [Table 17](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 11$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

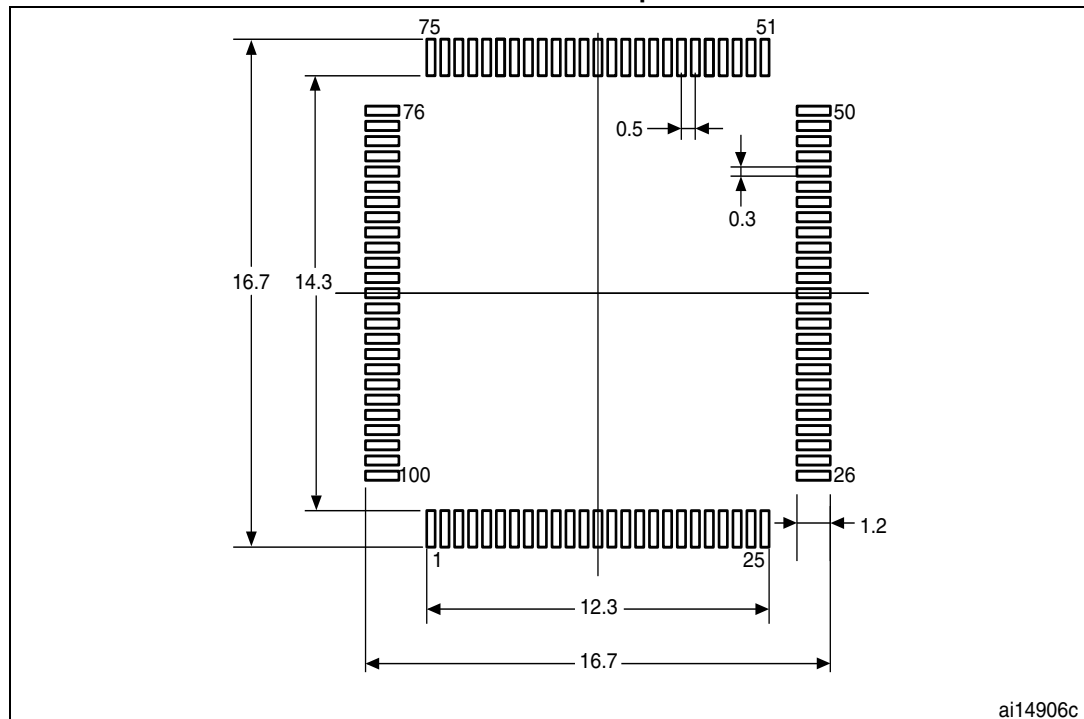
Refer to [Section 5.3.20: I/O port characteristics](#) for more details on the input/output characteristics.

Table 117. LQPF100, 14 x 14 mm 100-pin low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 83. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.